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TABLE OF CONTENTS

<p>A WIDEBAND AND HIGH EFFICIENCY KA-BAND GAN DOHERTY POWER AMPLIFIER FOR 5G COMMUNICATIONS</p> <p style="padding-left: 20px;"><i>Yutaro Yamaguchi, Keigo Nakatani, Shintaro Shinjo</i></p>	1
<p>MODELING THE TEMPERATURE DEPENDENCE OF SHEET AND CONTACT RESISTANCES IN SIGE:C HBTS FROM 4.3 TO 423 K</p> <p style="padding-left: 20px;"><i>Xiaodi Jin, Christoph Weimer, Yaxin Zhang, Michael Schröter</i></p>	5
<p>AN OVER 220-GHZ-BANDWIDTH DISTRIBUTED ACTIVE POWER COMBINER IN 250-NM INP DHBT</p> <p style="padding-left: 20px;"><i>Teruo Jyo, Munehiko Nagatani, Minoru Ida, Miwa Mutoh, Hitoshi Wakita, Naoki Terao, Hideyuki Nosaka</i></p>	9
<p>128-GS/S 1-TO-4 SIGE ANALOG DEMULTIPLEXER WITH 36-GHZ BANDWIDTH FOR 6-BIT DATA CONVERTERS</p> <p style="padding-left: 20px;"><i>Philipp Thomas, Tobias Tannert, Markus Grözing, Manfred Berroth</i></p>	13
<p>ROBUST-5W RECONFIGURABLE S/X-BAND GAN LNA USING A 90NM T-GATE GAN HEMT TECHNOLOGY</p> <p style="padding-left: 20px;"><i>Kevin W. Kobayashi, Vipin Kumar, Charles Campbell, Shuoqi Chen, Yu Cao, Jose Jimenez</i></p>	17
<p>18-44GHZ K/KA-BAND ROBUST-35.5DBM RECONFIGURABLE 90NM GAN HEMT LNA</p> <p style="padding-left: 20px;"><i>Kevin W. Kobayashi, Vipin Kumar, Charles Campbell, Shuoqi Chen, Yu Cao</i></p>	21
<p>A KU-BAND 70-W CLASS GAN INTERNALLY MATCHED HIGH POWER AMPLIFIER WITH WIDE OFFSET FREQUENCIES OF UP TO 400 MHZ FOR MULTI-CARRIER SATELLITE COMMUNICATIONS</p> <p style="padding-left: 20px;"><i>Takaaki Yoshioka, Kenji Harauchi, Takumi Sugitani, Takashi Yamasaki, Hiroaki Ichinohe, Miyo Miyashita, Kazuya Yamamoto, Seiki Goto</i></p>	25
<p>CURRENT COLLAPSE AND KINK EFFECT IN GAN RF HEMTS: THE KEY ROLE OF THE EPITAXIAL BUFFER</p> <p style="padding-left: 20px;"><i>Michael J. Uren, Martin Kuball</i></p>	29
<p>HICUM/L2: EXTENSIONS OVER THE LAST DECADE</p> <p style="padding-left: 20px;"><i>M. Schröter, A. Pawlak, A. Mukherjee, D. Celi, M. Krattenmacher</i></p>	37
<p>DEPENDENCE OF AM/PM NON-LINEARITY ON SOURCE FIELD-PLATE IN GAN HEMTS</p> <p style="padding-left: 20px;"><i>Sourabh Khandelwal, Petra Hammes, Marek Schmidt-Szalowski, Amit Dikshit, Menno Clerk</i></p>	41
<p>ULTRA-HIGH SPEED INP/GAASSB-BASED TYPE-II DOUBLE-HETEROJUNCTION BIPOLAR TRANSISTORS AND TRANSFER TECHNOLOGY ONTO SIC SUBSTRATE</p> <p style="padding-left: 20px;"><i>Yuta Shiratori, Takuya Hoshi, Hideaki Matsuzaki</i></p>	45
<p>COMPACT MODELING OF SIGE HBTS FOR DESIGN OF CRYOGENIC CONTROL AND READOUT CIRCUITS FOR QUANTUM COMPUTING</p> <p style="padding-left: 20px;"><i>Hanbin Ying, Sunil G. Rao, Jeffrey W. Teng, Milad Frounchi, Markus Müller, Xiaodi Jin, Michael Schröter, John D. Cressler</i></p>	49
<p>DESIGN OF AN 18–50 GHZ SIGE HBT CASCODE NON-UNIFORM DISTRIBUTED POWER AMPLIFIER</p> <p style="padding-left: 20px;"><i>Seokchul Lee, Inchan Ju, Yunyi Gong, Adilson S. Cardoso, Jeffrey D. Connor, Moon-Kyu Cho, John D. Cressler</i></p>	53

CIRCUIT-LEVEL SAFE-OPERATING-AREA OF A HIGH-SPEED SIGE BICMOS WIRELINE DRIVER	57
<i>Arya Moradinia, Rafael P. Martinez, Jeffrey W. Teng, Nelson Sepúlveda-Ramos, Harrison Lee, John D. Cressler</i>	
ANALOG/MIXED-SIGNAL INTEGRATED CIRCUITS FOR QUANTUM COMPUTING	62
<i>Joseph C Bardin</i>	
TRENDS IN IMAGING RADARS POWERED BY MODERN SILICON	70
<i>Sherif S. Ahmed</i>	
FAST PIXEL SENSORS FOR IONIZING PARTICLES INTEGRATED IN SIGE BICMOS	74
<i>Lorenzo Paolozzi, Giuseppe Iacobucci, Pierpaolo Valerio</i>	
MODELING AND CHARACTERIZATION OF HBT LIMITS	80
<i>A. J. Scholten</i>	
ROBUST EXTRACTION OF CARDIFF MODEL PARAMETERS FROM APPROPRIATELY TAILORED MEASURED LOAD-PULL DATA	88
<i>Paul J Tasker</i>	
REVERSE INTERMODULATION IN MULTI-TONE ARRAY TRANSMITTERS	93
<i>Anton N. Atanasov, Mark S. Oude Alink, Frank E. Van Vliet</i>	
A 120 GS/S 2:1 ANALOG MULTIPLEXER WITH HIGH LINEARITY IN SIGE-BICMOS TECHNOLOGY	97
<i>Michael Collisi, Michael Möller</i>	
RF PERFORMANCE OF GAN-BASED GRADED-CHANNEL HEMTS	101
<i>Nivedhita Venkatesan, Jeong Moon, Joel Wong, Bob Grabar, Michael Antcliffe, Peter Chen, Erdum Arkun, Isaac Khalaf, David Fanning, Patrick Fay</i>	
THE DARPA MILLIMETER WAVE DIGITAL ARRAYS (MIDAS) PROGRAM	105
<i>Timothy M. Hancock, Steven Gross, James McSpadden, Lawrence Kushner, Jason Milne, Jon Hacker, Ryan Walsh, Craig Hornbuckle, Charles Campbell, Kevin Kobayashi</i>	
A NEW WIDEBAND, LOW INSERTION LOSS SIGE DIGITAL STEP ATTENUATOR A NEW WIDEBAND, LOW INSERTION LOSS SIGE DIGITAL STEP ATTENUATOR	109
<i>Clifford D. Cheon, Moon-Kyu Cho, Sunil G. Rao, Adilson S. Cardoso, Jeffrey D. Connor, John D. Cressler</i>	
MONOLITHICALLY INTEGRATED GAN+CMOS LOGIC CIRCUITS DESIGN AND ELECTRO-THERMAL ANALYSIS FOR HIGH-VOLTAGE APPLICATIONS	114
<i>Pilsoon Choi, Bugra Kanargi, Kenneth E. Lee, Chirn-Chye Boon, Evelyn Wang, Chuan Seng Tan, Dimitri A. Antoniadis, Eugene A. Fitzgerald</i>	
BROADBAND RECONFIGURABLE TRANSCEIVERS IN SIGE	118
<i>Gregory M. Flewelling</i>	
A 117 GHZ DUAL-MODULUS PRESCALER WITH INDUCTIVE PEAKING FOR A PROGRAMMABLE FREQUENCY DIVIDER	122
<i>L. Polzin, M. Van Delden, N. Pohl, K. Aufinger, T. Musch</i>	
SLC-ASM-HEMT: AN ACCURATE COMPACT MODEL FOR SLCFET RF SWITCH	126
<i>Sourabh Khandelwal, Brian Novak, Jordan Merkel, Ken Nagamatsu, Justin Parke, Mark Yu, Patrick Shea, Robert Howell</i>	

MICROWAVE PERFORMANCE OF FERROELECTRIC-GATED GAN HEMTS	130
<i>Chunlei Wu, Jeffrey Smith, Suman Datta, Yu Cao, Jinqiao Xie, Edward Beam, Patrick Fay</i>	
230–305 GHZ, > 10-DBM-OUTPUT-POWER WIDEBAND POWER AMPLIFIER USING LOW-Q NEUTRALIZATION TECHNIQUE IN 60-NM INP-HEMT TECHNOLOGY	134
<i>Hiroshi Hamada, Takuya Tsutsumi, Adam Pander, Masahito Nakamura, Go Itami, Hideaki Matsuzaki, Hiroki Sugiyama, Hideyuki Nosaka</i>	
PHOTONIC-ELECTRONIC ULTRA-BROADBAND SIGNAL PROCESSING: CONCEPTS, DEVICES, AND APPLICATIONS	138
<i>C. Koos, S. Randel, W. Freude, T. Zwick, J. C. Scheytt, J. Witzens, M. Walther, T. Harter, S. Ummethala, C. Kieninger, H. Zwickel, P. Marin-Palomo, S. Muehlbrandt, C. Füllner, J. Schaefer, S. Gudyriev, A. Zazzi, J. Müller, A. Tessmann</i>	
PHYSICS OF HOT CARRIER DEGRADATION UNDER SATURATION MODE OPERATION IN SIGE HBTS.....	141
<i>Uppili S. Raghunathan, Pui Yee, Dave Brochu, Vibhor Jain, Harrison P. Lee, John D. Cressler, Dimitris P. Ioannou</i>	
HIGH PERFORMANCE 150 MM RF GAN TECHNOLOGY WITH LOW MEMORY EFFECTS	145
<i>K. Moore, B. Green, S. Klingbeil, C. Rampley, P. Renaud, D. Burdeaux, D. Hill, C. Zhu, J. Wan, J. Finder, K. Kim, C. Gaw, T. Arnold, F. Vanaverbeke, R. Embar, P. Rashev, M. Masood</i>	
A 20-33 GHZ DIRECT-CONVERSION TRANSMITTER IN 45-NM SOI CMOS	149
<i>Tiantong Ren, Sandeep Hari, Brian A. Floyd</i>	
IMPACT OF LARGE-SIGNAL OPERATION ON DC OPERATING POINT OF HORIZONTAL CURRENT BIPOLAR TRANSISTOR.....	153
<i>Željko Osrecki, Josip Žilak, Marko Koracic, Tomislav Suligoj</i>	
A FULLY INTEGRATED 20-500-GHZ COHERENT DETECTOR WITH 2-HZ FREQUENCY RESOLUTION	157
<i>Mostafa Hosseini, Aydin Babakhani</i>	
USING CHANNEL PHYSICAL RELATIONSHIPS IN PHEMT MODELING.....	161
<i>Yingying Yang, Xiao-Ping Li, Cristian Cismaru, Ravi Ramanathan</i>	
A 28–37 GHZ TRIPLE-STAGE TRANSFORMER-COUPLED SIGE LNA WITH 2.5 DB MINIMUM NF FOR LOW POWER WIDEBAND PHASED ARRAY RECEIVERS.....	165
<i>Abdulrahman A. Alhamed, Gabriel M. Rebeiz</i>	
DESIGN OF A WIDEBAND, 4 – 42.5 GHZ LOW NOISE AMPLIFIER IN 0.25 μM GAAS PHEMT TECHNOLOGY	169
<i>M. Sakalas, P. Sakalas</i>	
A 10 MW LNA WITH TEMPERATURE COMPENSATION FOR 24 GHZ RADAR APPLICATIONS IN SIGE BICMOS	173
<i>Vadim Issakov, Andreas Werthof</i>	
MATERIALS AND DEVICE ENGINEERING FOR HIGH-PERFORMANCE GALLIUM OXIDE DEVICES.....	177
<i>Zhanbo Xia, Nidhin Kurian Kalarickal, Siddharth Rajan</i>	
A COMMERCIAL FOUNDRY PERSPECTIVE OF SIGE BICMOS PROCESS TECHNOLOGIES.....	183
<i>Edward Preisler</i>	

SIGE MICROWAVE PHOTOTRANSISTORS FOR MICROWAVE-PHOTONICS APPLICATIONS.....	188
<i>Jean-Luc Polleux, Zerihun G. Tegegne, Marc D. Rosales, Francesco Peressutti, Jean-Marc Laheurte, Catherine Algani, Jacopo Nanni, Giovanni Tartarini, Carlos Viana</i>	
MILLIMETER-WAVE GAN SSPAS: TECHNOLOGY TO POWER 5G AND THE FUTURE.....	195
<i>James Schellnberg</i>	
DEVICE SCALING ROADMAP AND ITS IMPLICATIONS FOR LOGIC AND ANALOG PLATFORM.....	202
<i>Alessio Spessot, Bertrand Parvais, Amita Rawat, Kenichi Miyaguchi, Pieter Weckx, Doyoung Jang, Julien Ryckaert</i>	
CONFIGURABLE AND SCALABLE HIGH-SIDE OR LOW-SIDE DRIVER IN BICMOS WITH 20DB μ V EMISSION AT 88MHZ	210
<i>S. N. Easwaran, S. V. Kashyap, D. Sreedharan, R. Hubbard, V. Devarajan, W. Ray</i>	
ULTRA BROADBAND LOW-POWER 70 GHZ ACTIVE BALUN IN 130-NM SIGE BICMOS	214
<i>Aniello Franzese, Mohamed H. Eissa, Thomas Mausolf, Dietmar Kissinger, Renato Negra, Andrea Malignaggi</i>	
III-V NANOWIRE MOSFETS: RF-PROPERTIES AND APPLICATIONS.....	218
<i>Lars-Erik Wernersson</i>	
A HIGH EFFICIENCY 4–18 GHZ GAN MMIC POWER AMPLIFIER BASED ON 90NM T-GATE GAN HEMT TECHNOLOGY	222
<i>Shuoqi Chen, Vipin Kumar, Yu Cao</i>	
A HIGHLY-EFFICIENT 120 GHZ AND 240 GHZ SIGNAL SOURCE IN A SIGE-TECHNOLOGY	226
<i>Florian Vogelsang, David Starke, Jonathan Wittemeier, Holger Rücker, Nils Pohl</i>	
A 24 GHZ SUB-HARMONICALLY PUMPED RESISTIVE MIXER IN GAN HEMT TECHNOLOGY	230
<i>Yu Yan, Thanh Ngoc Thi Do, Dan Kuylentierna</i>	
A 108-GBPS, 162-MW CHERRY-HOOPER TRANSIMPEDANCE AMPLIFIER.....	233
<i>Luis A. Valenzuela, Aaron Maharry, Hector Andrade, Clint L. Schow, James F. Buckwalter</i>	

Author Index